

silicon transistors

UHF/VHF power transistors
NPN type

T-37-01

Type	Rated Breakdown Voltages			Power Out				C _{OB} (pF)	f _P (MHz)	Case
	V _{CB}	V _{CE}	V _{EB}	V _{CE}	f _o (MHz)	P _{IE} (W)	P _O (W)			
2N3375	65	40	4.0	28	400	1.0	3.0	12.0	500 Typ	TO-60
2N3553	65	40	4.0	28	175	.25	2.5	12.0	350	TO-5
2N3632	65	40	4.0	28	175	3.5	13.5	25.0	250	TO-60
2N3733	65	40	4.0	28	400	4.0	10.0	25.0	250	TO-60
2N3866	55	30	3.5	28	400	0.1	1.0	3.0	500	TO-5
2N3924	36	18	4.0	13.6	175	1.0	4.0	20.0	250	TO-5
2N3928	36	18	4.0	13.6	175	2.0	7.0	20.0	250	TO-60
2N3927	36	18	4.0	13.6	175	4.0	12.0	45.0	200	TO-60
2N4012	65	40	4.0	13.6	1000	1.0	2.5	10.0	350	TO-60
2N4040	60	40	4.0	28	400	3.0	8.0	15.0	400	MT-72j
2N4041	60	40	4.0	28	400	1.0	3.3	8.0	400	MT-72j
2N4127	60	40	4.0	25	175	2.5	13.5	25.0	300	MT-72j
2N4128	60	40	4.0	25	175	6.0	24.0	45.0	200	MT-72j
2N4427	40	20	2.0	12	175	0.1	1.0	4.0	500	TO-5
2N4428	55	35	3.5	28	500	.075	.75	3.5	700	TO-5
2N4429	55	35	3.5	28	1000	.25	1.0	3.5	700	MT-72j
2N4430	55	40	3.5	28	1000	.7	2.5	5.0	600	MT-66
2N4431	55	40	3.5	28	1000	1.15	5.0	10.0	600	MT-66
2N4440	65	40	4.0	28	400	1.7	5.0	12.0	500 Typ	TO-60

Type	Rated Breakdown Voltages			Power Out				C _{OB} (pF)	f _i (MHz)	Case
	V _{CB}	V _{CE}	V _{EB}	V _{CE}	f _o (MHz)	P _{IE} (W)	P _O (W)			
2N4933	70	35	4.0	24	70	3.5	20.0	85.0	200	TO-60
2N5016	65	30	4.0	28	400	5.0	15.0	25.0	500	TO-60
2N5070	65	30	4.0	28	30	.625	12.5	85	100	TO-60
2N5071	65	30	4.0	24	70	3.0	24.0	85	100	TO-60
2N5090	55	30	3.5	28	400	0.2	1.2	3.5	500	TO-60
2N5102	55	30	3.5	28	400	0.2	1.2	3.5	500	TO-60
2N5108	55	30	3.0	28	1000	.316	1.0	3.0	1200	TO-5
2N5109	40	20	3.0	28	1000	.32	1.0	3.5	1200	TO-5
2N5421	36	18	4.0	13.5	175	.125	1.0	5.0	300	TO-5
2N5423	36	18	4.0	13.5	175	1.25	5.0	25.0	300	TO-60
2N5424	36	18	4.0	13.5	175	4.1	13.0	45.0	250	TO-60
2N5591	36	18	4.0	13.6	175	9.5	25.0	120.0	200	MT-72
2N5641	65	35	4.0	28	175	1.0	7.0	15.0	300	MT-71
2N5642	65	35	4.0	28	175	2.8	20.0	35.0	250	MT-72e
2N5643	65	35	4.0	28	175	8.0	40.0	65.0	200	MT-72e
2N6080	36	18	4.0	13.6	100		4	20	200	MT-72h
2N6081	36	18	4.0	13.6	100		15	85	200	MT-72h
2N6082	36	18	4.0	13.6	100		25	130	200	MT-72h
2N6083	36	18	4.0	13.6	100		30	130	200	MT-72h
2N6084	36	18	4.0	13.6	100		40	200	200	MT-72h

germanium transistors

diffused-base MESA transistors
ultra-high-speed switching

Type	Polarity	BVCBO	BVCES	Typ. Gain HFE	f _{cb} Avg. mc	V _{sat} Avg. Volts	Case
		Max. Volts	Max. Volts				
2N705	PNP	-15	-15	25	300	0.125	TO-18
2N705A	PNP	-15	-15	40	-	0.125	TO-18
2N710	PNP	-15	-15	25	300	0.125	TO-18
2N710A	PNP	-15	-15	70	-	0.125	TO-18
2N711	PNP	-12	-12	80	300	0.125	TO-18
2N711A	PNP	-15	-14	80	-	0.125	TO-18
2N711B	PNP	18	15	80	320*	0.18	TO-18
2N702	PNP	-12	-12	20	-	0.125	TO-18
2N797	NPN	20	7	40	600	0.5	TO-18
2N828	PNP	-15	-15	25	-	0.125	TO-18
2N837	PNP	12	12	30	-	0.18	TO-18
2N855	NPN	12	11	30	1000	0.3	TO-18
2N855A	NPN	12	11	30	1000	0.3	TO-18
2N860	PNP	15	15	20	460*	0.125	TO-18
2N861	PNP	12	12	20	460*	0.125	TO-18
2N862	PNP	12	12	20	460*	0.125	TO-18
2N863	PNP	12	12	20	460*	0.18	TO-18
2N864	PNP	15	15	60	460*	0.125	TO-18
2N864A	PNP	15	15	60	-	0.10	TO-18
2N865	PNP	12	12	40	460*	0.125	TO-18

Type	Polarity	BVCBO	BVCES	Typ. Gain HFE	f _{cb} Avg. mc	V _{sat} Avg. Volts	Case
		Max. Volts	Max. Volts				
2N866	PNP	12	12	40	460*	0.125	TO-18
2N867	PNP	12	-	40	460*	0.11	TO-18
2N868	PNP	15	15	20	320*	0.18	TO-18
2N869	PNP	12	12	17	320*	0.18	TO-18
2N870	PNP	12	12	20	320*	0.18	TO-18
2N871	PNP	7	7	20	320*	0.18	TO-1C
2N872	PNP	15	15	40	320*	0.18	TO-18
2N873	PNP	12	12	40	320*	0.18	TO-18
2N874	PNP	12	12	40	320*	0.18	TO-18
2N875	PNP	7	7	40	320*	0.18	TO-18
2N885	PNP	15	-	40	-	0.10	TO-18
2N894	PNP	15	15	45	-	0.18	TO-18
2N1692	PNP	25	25	10	500	0.4	TO-102
2N1693	PNP	25	25	9	450	0.4	TO-102
2N2168	PNP	40	40	80	60	-	TO-1
2N2169	PNP	40	40	80	102	-	TO-1
2N2190	PNP	60	60	80	60	-	TO-1
2N2191	PNP	60	60	80	102	-	TO-1
2N2482	NPN	20	12	15	600	2.	TO-18

case outline drawings

T01

T03

T05

T018

T033

T036

T039

T046

T059

T061

T063

T066

T072

T082

F8

Y220/T0220

NOTES:

1. Refer to rules for dimensioning semiconductor product outlines including in Publication No. 81, Figure A, Metal Terminal Conventions, applicable.
2. Flange ϕ and Full Power Terminal Configuration, applicable.
3. Alternative lead configurations allowed within C and S.
4. Two contours allowed within M and P.
5. Chassis optional.
6. Position of lead to be measured $\pm .010$ below seating plane.
7. Fraction of lead to be retained $\pm .010$ cross section of diameter ϕ .

TERMINAL CONFIGURATION	TERMINAL POSITION	TERMINAL TYPE	TERMINAL MATERIAL	TERMINAL FINISH	TERMINAL DIMENSIONS	TERMINAL TOLERANCES	TERMINAL SPACING	TERMINAL SPACING TOLERANCES	TERMINAL SPACING	TERMINAL SPACING TOLERANCES	TERMINAL SPACING	TERMINAL SPACING TOLERANCES	TERMINAL SPACING	TERMINAL SPACING TOLERANCES	TERMINAL SPACING	TERMINAL SPACING TOLERANCES	TERMINAL SPACING	TERMINAL SPACING TOLERANCES
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